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NTE2673 (NPN) & NTE2674 (PNP) Silicon Complementary Transistors General Purpose Power TO220FP Type Package

Features:

- Low Collector–Emitter Saturation Voltage: $V_{CE(sat)} = 0.5V$ Typ ($I_C/I_B = 2A/0.2A$)

Absolute Maximum Ratings: ($T_A = +25^\circ C$ unless otherwise specified)

Collector–Base Voltage, V_{CBO}	60V
Collector–Emitter Voltage, V_{CEO}	50V
Emitter–Base Voltage, V_{EBO}	5V
Collector Current, I_C	
Continuous	3A
Peak (Note 1)	4.5A
Collector Power Dissipation ($T_C = +25^\circ C$, Note 2), P_D	25W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	–55° to +150°C

Note 1. Single pulse: Pulse Width = 10ms.

Note 2. Printed circuit board 1.7mm thick, collector copper plating 1cm² or larger.

Electrical Characteristics: ($T_A = +25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 50\mu A$	60	–	–	V
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1mA$	50	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 50\mu A$	5	–	–	V
Collector Cutoff Current	I_{CBO}	$V_{CE} = 40V$	–	–	1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4V$	–	–	1	μA
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 2A, I_B = 200mA$, Note 3	–	0.5	1.0	V
DC Current Transfer Ratio	h_{FE}	$I_C = 500mA, V_{CE} = 3V$, Note 3	60	–	320	
Transition Frequency	f_T	$I_E = -500mA, V_{CE} = 5V, f = 30MHz$, Note 3	–	90	–	MHz
Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0A, f_{test} = 1MHz$	–	40	–	pF

Note 3. Measured using pulse current.

